

ABSTRACT

A semiconductor device may include a first active pattern extending in a first direction and having a first width in a second direction, a second active pattern extending in the first direction and having a second width in the second direction that is less than the first width, first gate structures extending on the first active pattern, second gate structures extending on the second active pattern, a first source/drain region on the first active pattern between the first gate structures, a second source/drain region on the second active pattern between the second gate structures, a first fin spacer on a side surface of the first source/drain region, and a second fin spacer on a side surface of the second source/drain region. A height of the first fin spacer in a third direction may be less than a height of the second fin spacer in the third direction.

FIG. 4A